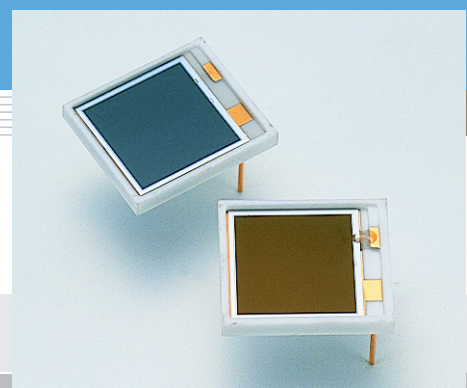


# Si PIN photodiode

## S3590-18/-19

Large area Si PIN photodiode for scintillation counting



### Features

- Suitable for coupling with blue scintillator (LSO, GSO, etc.)
- Internal quantum efficiency: 100 % ( $\lambda=420$  nm)
- S3590-19: bare chip type (without window)

### Applications

- Radiation detection (PET, etc.)
- X-ray detection

### ■ Absolute maximum ratings

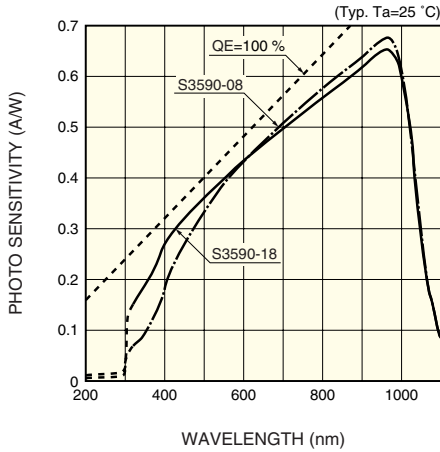
Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	100	V
Power dissipation	P	100	mW
Operating temperature	$T_{opr}$	-20 to +60	°C
Storage temperature	$T_{stg}$	-20 to +80	°C

### ■ Electrical and optical characteristics ( $T_a=25$ °C)

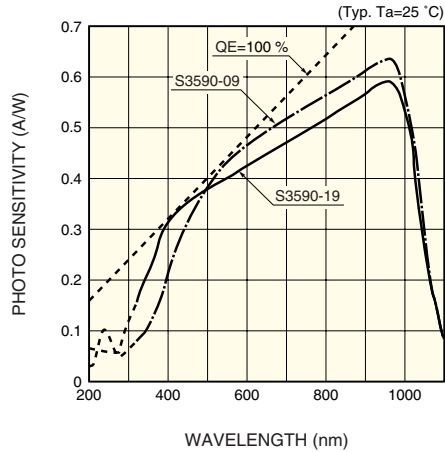
Parameter	Symbol	Condition	S3590-18			S3590-19			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	$\lambda$		-	320 to 1100	-	-	320 to 1100	-	nm
Peak sensitivity wavelength	$\lambda_p$		-	960	-	-	960	-	nm
Photo sensitivity	S	$\lambda=\lambda_p$	-	0.65	-	-	0.58	-	A/W
		$\lambda=420$ nm (LSO)	-	0.28	-	-	0.33	-	A/W
		$\lambda=480$ nm (BGO)	-	0.34	-	-	0.37	-	A/W
		$\lambda=540$ nm (CsI)	-	0.38	-	-	0.4	-	A/W
Short circuit current	$I_{sc}$	100 lx	-	100	-	-	86	-	$\mu$ A
Dark current	$I_D$	$V_R=70$ V	-	4	10	-	4	10	nA
Temperature coefficient of $I_D$	$T_{CID}$		-	1.12	-	-	1.12	-	times/°C
Cut-off frequency	$f_c$	$V_R=70$ V, -3 dB $R_L=50$ $\Omega$	-	40	-	-	40	-	MHz
Terminal capacitance	$C_t$	$V_R=70$ V, $f=1$ MHz	-	40	-	-	40	-	pF
Noise equivalent power	NEP		-	$7.6 \times 10^{-14}$	-	-	$7.6 \times 10^{-14}$	-	W/Hz <sup>1/2</sup>

## ■ Spectral response

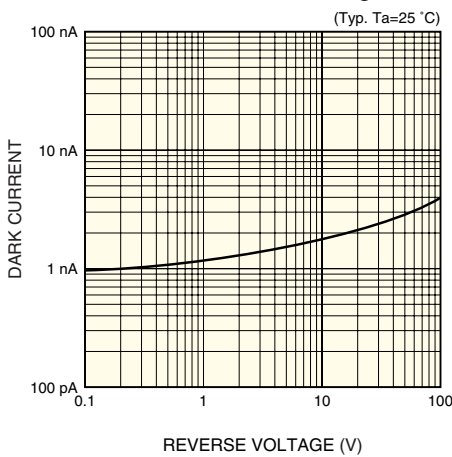
**S3590-18**



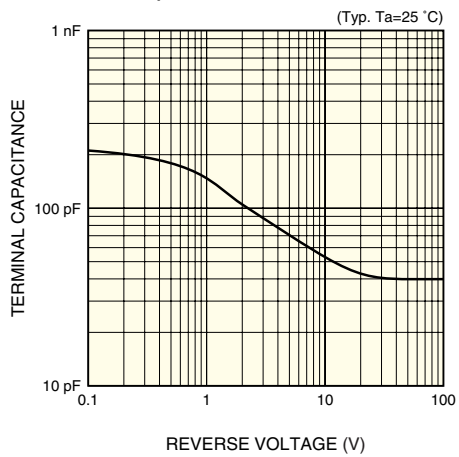
**S3590-19 (Bare chip type)**



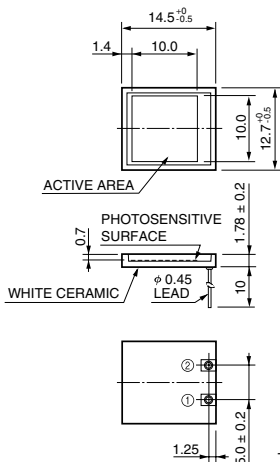
## ■ Dark current vs. reverse voltage



## ■ Terminal capacitance vs. reverse voltage



## ■ Dimensional outline (unit: mm)



The coating resin may extend a maximum of 0.1 mm beyond the upper surface of the package.

KPINA0098EA

# HAMAMATSU

Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2003 Hamamatsu Photonics K.K.

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation, 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH, Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741